

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
SETI-0002DIV

In Re Application Of:

Khan et al.

Serial No.
10/647,714

Filing Date
8/25/2003

Examiner
Unknown

Group Art Unit
Unknown



Title: **METAL OXIDE SEMICONDUCTOR HETEROSTRUCTURE FIELD EFFECT TRANSISTOR**

Address to:

**Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

OR

☐ the fee set forth in 37 CFR 1.17(p).

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(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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- ☐ Charge the amount of _____
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Dated: **October 30, 2003**

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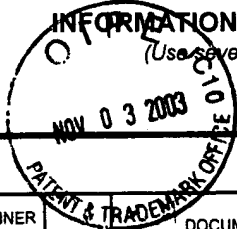
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INFORMATION DISCLOSURE CITATION

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SETI-0002

SERIAL NO.

09/966,559

Khan et al.

FILING

09/27/2001

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2818

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

			"Optoelectronic GaN-based Field Effect Transistors," M. S. Shur et al., SPIE, Vol. 2397, pp. 294-303, Feb. 7, 1995.
			"High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, pp. 377-380, Charlottesville, VA, Dec. 1997.

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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SERIAL NO. 09/966,559

FILING
09/27/2001

GROUP	2818
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[illegible][illegible]

			"Low Dark Current Transparent Schottky Barrier UV Detectors," G. Simin et al., ICNS3, Montpellier, June 1999.

DATE CONSIDERED

Form PTO-A820
(also form PTO-1449)

Patent and Trademark Office * U.S. DEPARTMENT OF COMMERCE

INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

SETI-006

Application Number

09/966559

Applicant(s)

Khan et al.

Filing Date

9/27/2001

Group Art Unit

2818

*EXAMINER

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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Shur, M.S. and Khan, M.A., "Wide Band Gap Semiconductors. Good Results and Great Expectations," Paper presented at 23rd Int. Symp. Compound Semiconductors, St. Petersburg, Russia, 23-27 September 1996, pp. 25-31.

Khan, M.A. et al., "AlGa_N/Ga_N Metal Oxide Semiconductor Heterostructure Field Effect Transistor," IEEE Electron Device Letters, Vol. 21, No. 2, February 2000, pp. 63-65.

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